



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

**SURFACE MOUNT
PNP SILICON Transistor**

VOLTAGE 60 Volts CURRENT 3 Ampere

CHT2955ZGP

APPLICATION

- * Telephony and professional communication equipment.
- * Other switching applications.

FEATURE

- * Small flat package. (SC-73/SOT-223)
- * Suitable for high packing density.
- * High saturation current capability.

CONSTRUCTION

*PNP SILICON Transistor

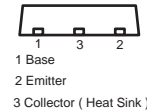
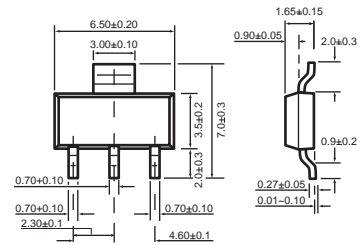
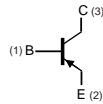
MARKING

* ZDP



SC-73/SOT-223

CIRCUIT



Dimensions in millimeters

SC-73/SOT-223

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	-	-100	V
V _{CE0}	collector-emitter voltage	open base	-	-60	V
V _{EB0}	emitter-base voltage	open collector	-	-7.0	V
I _C	collector current (DC)		-	-6.0	A
I _B	Base Current		-	-3.0	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	2	W
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC CURVES (CHT2955ZGP)

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CEO}	collector cut-off current	$V_{CE} = -30\text{ V}$	–	-700	μA
I_{EBO}	emitter cut-off current	$V_{EB} = -7.0\text{ V}$	–	-5.0	mA
h_{FE}	DC current gain	$I_C = -4.0\text{ A}; V_{CE} = -4\text{ V}$ $I_C = -6.0\text{ A}; V_{CE} = -4\text{ V}$	20 5.0	70 –	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -4.0\text{ A}, I_B = -400\text{ mA}$	–	-1.1	V
V_{BEON}	base-emitter saturation voltage	$I_C = -4.0\text{ A}; V_{CE} = -4\text{ V}$	–	-1.5	V
f_T	transition frequency	$I_C = -500\text{ mA}; V_{CE} = 10\text{ V};$ $f = 1.0\text{ MHz}$	2.5	–	MHz